

High Speed Quad SPST CMOS Analog Switch

DESCRIPTION

The DG201HS is an improved monolithic device containing four independent analog switches. It is designed to provide high speed, low error switching of analog signals. Combining low on-resistance ($25\ \Omega$) with high speed (t_{on} : 38 ns), the DG201HS is ideally suited for high speed data acquisition requirements.

To achieve high voltage ratings and superior switching performance, the DG201HS is built on a proprietary high-voltage silicon-gate process. An epitaxial layer prevents latchup.

Each switch conducts equally well in both directions when on, and blocks input voltages to the supply values, when off.

BENEFITS

- Faster throughput
- Higher accuracy
- Reduced pedestal error
- Upgrades existing designs
- Simple interfacing
- Replaces HI201HS, ADG201HS
- Space savings (TSSOP)

FEATURES

- Fast switching- t_{on} : 38 ns
- Low on-resistance: $25\ \Omega$
- Low leakage: 100 pA
- Low charge injection
- TTL/CMOS logic compatible
- Single supply compatibility
- High current rating: -30 mA
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

Note

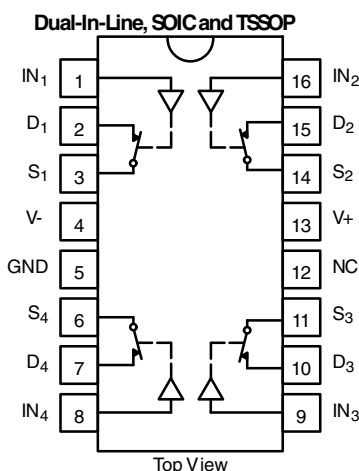
* This datasheet provides information about parts that are RoHS-compliant and / or parts that are non RoHS-compliant. For example, parts with lead (Pb) terminations are not RoHS-compliant. Please see the information / tables in this datasheet for details



APPLICATIONS

- Data acquisition
- Hi-Rel systems
- Sample and hold circuits
- Communication systems
- Automatic test equipment
- Integrator reset circuits
- Choppers
- Gain switching
- Avionics

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION



TRUTH TABLE	
LOGIC	SWITCH
0	On
1	Off

Note

- Logic "0" $\leq 0.8\text{ V}$; logic "1" $\geq 2.4\text{ V}$

ORDERING INFORMATION

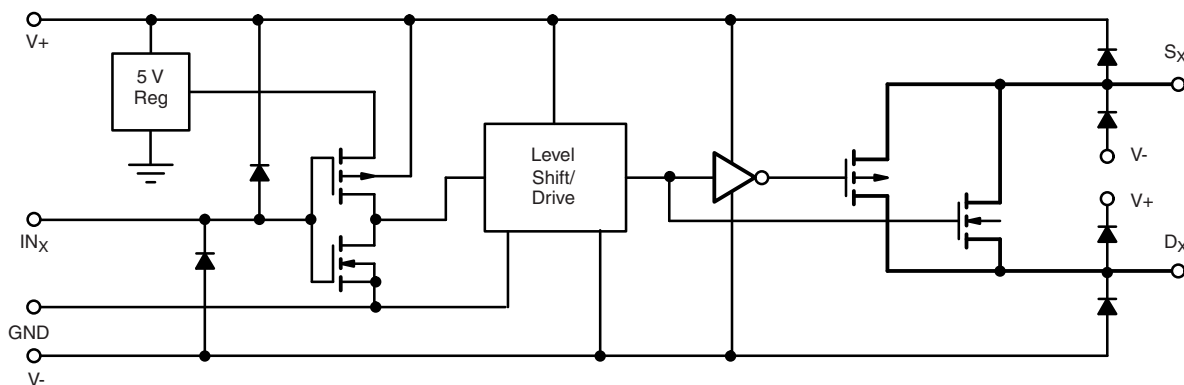
TEMP. RANGE	PACKAGE	PART NUMBER
-40 °C to +85 °C	16-pin narrow SOIC	DG201HSDY-E3 DG201HSDY-T1-E3
	16-pin TSSOP	DG201HSDQ-E3 DG201HSDQ-T1-E3
	16-pin plastic DIP	DG201HSDJ-E3

ABSOLUTE MAXIMUM RATINGS

PARAMETER		LIMIT	UNIT
Voltages referenced, V+ to V-		44	V
GND		25	
Digital inputs ^a , V _S , V _D		(V-) - 4 to (V+) + 4 or 30 mA, whichever occurs first	
Current (any terminal)		30	mA
Peak current S or D (pulsed at 1 ms, 10 % duty cycle max.)		100	
Storage temperature	(A suffix)	-65 to +150	°C
	(D suffix)	-65 to +125	
Power dissipation (package) ^b	16-pin plastic DIP ^c	470	mW
	16-pin narrow body SOIC and TSSOP ^e	600	

Notes

- Signals on S_X, D_X, or IN_X exceeding V+ or V- will be clamped by internal diodes. Limit forward diode current to maximum current ratings
- All leads welded or soldered to PC board
- Derate 6 mW/°C above 75 °C
- Derate 12 mW/°C above 75 °C
- Derate 7.6 mW/°C above 75 °C

SCHEMATIC DIAGRAM (typical channel)

Fig. 1

**SPECIFICATIONS ^a**

PARAMETER	SYMBOL	TEST CONDITIONS UNLESS SPECIFIED V ₊ = 15 V, V ₋ = -15 V V _{IN} = 3 V, 0.8 V ^f	TEMP. ^b	TYP. ^c	A SUFFIX -55 °C to +125 °C		D SUFFIX -40 °C to +85 °C		UNIT
					MIN. ^d	MAX. ^d	MIN. ^d	MAX. ^d	
Analog Switch									
Analog signal range ^e	V _{ANALOG}		Full	-	V-	V+	V-	V+	V
Drain-source on-resistance	R _{DS(on)}	V _D = ± 10 V, I _S = 1 mA	Room	25	-	50	-	50	Ω
R _{DS(on)} match	ΔR _{DS(on)}		Full	-	-	75	-	75	
			Room	3	-	-	-	-	%
Source off leakage current	I _{S(off)}	V ₊ = 16.5 V, V ₋ = -16.5 V, V _D = ± 15.5 V, V _S = ± 15.5 V	Room	0.1	-1	1	-1	1	nA
			Full	-	-60	60	-20	20	
Drain off leakage current	I _{D(off)}		Room	0.1	-1	1	-1	1	
			Full	-	-60	60	-20	20	
Drain on leakage current	I _{D(on)}	Room	0.1	-1	1	-1	1		
		Full	-	-60	60	-20	20		
Digital Control									
Input voltage high	V _{INH}		Full	-	2.4	-	2.4	-	V
Input voltage low	V _{INL}		Full	-	-	0.8	-	0.8	
Input current	I _{INH} or I _{INL}	V _{IN} under test = 0.8 V, 3 V	Full	-	-1	1	-1	1	μA
Input capacitance	C _{IN}		Full	5	-	-	-	-	pF
Dynamic Characteristics									
Turn-on time	t _{on}	R _L = 1 kΩ, C _L = 35 pF, V _S = ± 10 V, V _{INH} = 3 V, see Fig. 2	Room	48	-	60	-	60	ns
			Full	-	-	75	-	75	
Turn-off time	t _{off1}		Room	30	-	50	-	50	
			Full	-	-	70	-	70	
	t _{off2}		Room	150	-	-	-	-	
Output setting time to 0.1 %	t _S		Room	180	-	-	-	-	
Charge injection	Q	C _L = 1 nF, V _S = 0 V, V _{GEN} = 0 V, R _{gen} = 0 Ω	Room	-5	-	-	-	-	pC
Source-off capacitance	C _{S(off)}	V _S = V _D = 0 V, f = 1 MHz	Room	8	-	-	-	-	pF
Drain-off capacitance	C _{D(off)}		Room	8	-	-	-	-	
Channel on capacitance	C _{D(on)}		Room	30	-	-	-	-	
Drain to source capacitance	C _{DS(off)}		Room	0.5	-	-	-	-	
Off isolation	OIRR	C _L = 10 pF, R _L = 1 kΩ, f = 100 kHz	Room	85	-	-	-	-	dB
Channel-to-channel crosstalk	X _{TALK}	Any other channel switches, C _L = 10 pF, R _L = 1 kΩ, f = 100 kHz	Room	100	-	-	-	-	
Power Supply									
Positive supply current	I ₊	V ₊ = 15 V, V ₋ = -15 V, V _{IN} = 0 V or 5 V	Room	4.5	-	-	-	-	mA
			Full	-	-	10	-	10	
Negative supply current	I ₋		Room	3.5	-	-	-	-	
			Full	-	-6	-	-6	-	
Power consumption ^c	P _C			Full	-	-	240	-	240

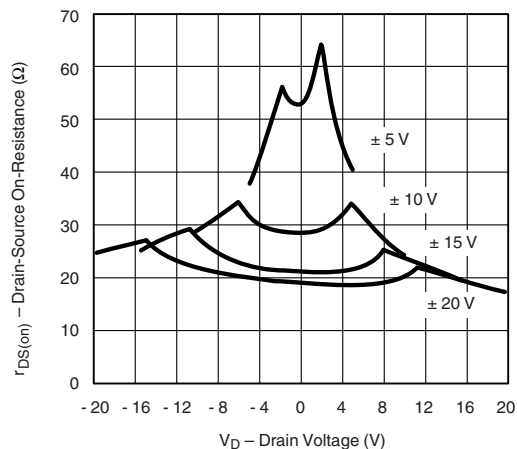
Notes

- a. Refer to "Process Option Flowchart"
b. Room = 25 °C, full = as determined by the operating temperature suffix
c. Typical values are for "Design Aid Only", not guaranteed nor subject to production testing
d. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this datasheet
e. Guaranteed by design, not subject to production test
f. V_{IN} = input voltage to perform proper function

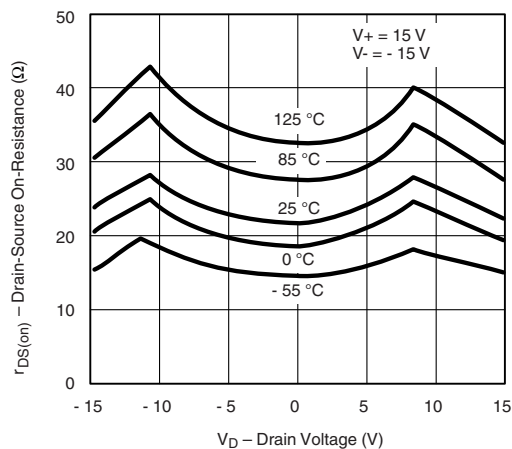
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



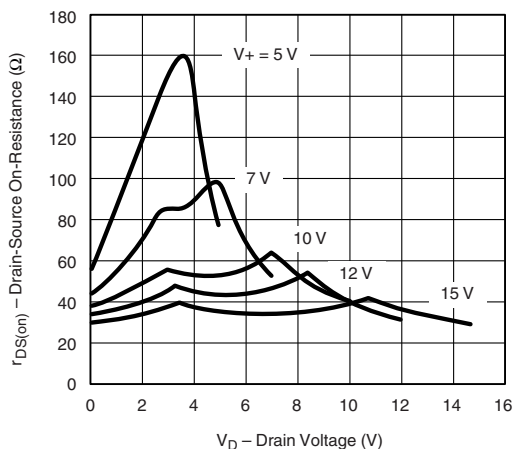
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



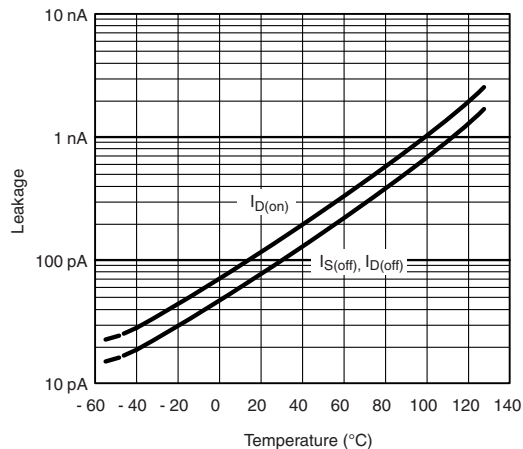
$R_{DS(on)}$ vs. V_D and Power Supply Voltages



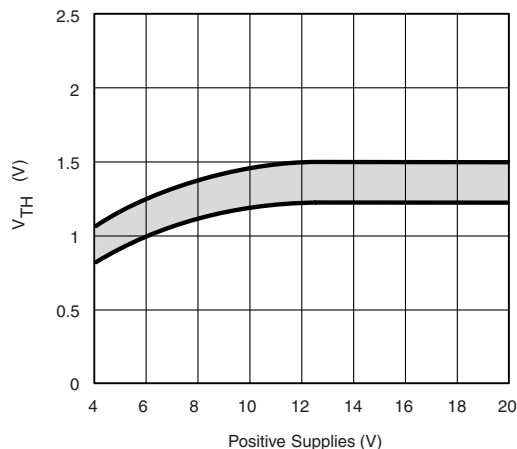
$R_{DS(on)}$ vs. V_D and Temperature



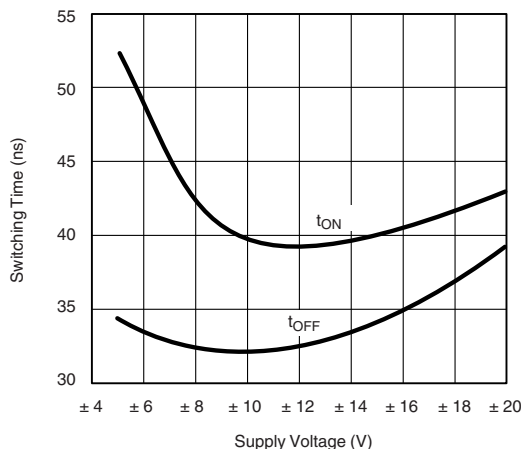
$R_{DS(on)}$ vs. V_D and Single Power Supply Voltages



Leakage Currents vs. Temperature



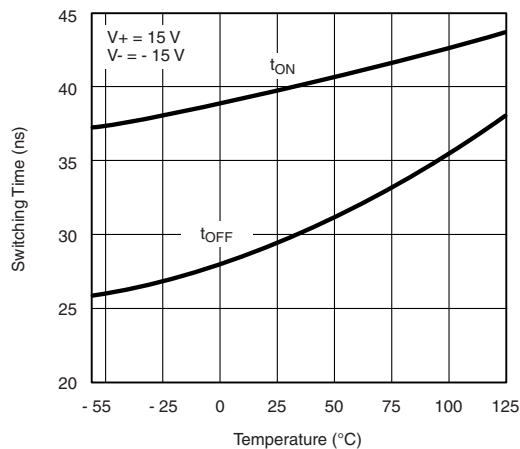
Input Switching Threshold vs. Supply Voltage



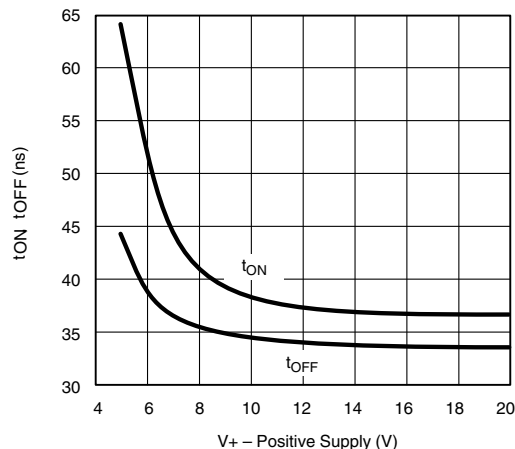
Switching Time vs. Power Supply Voltage



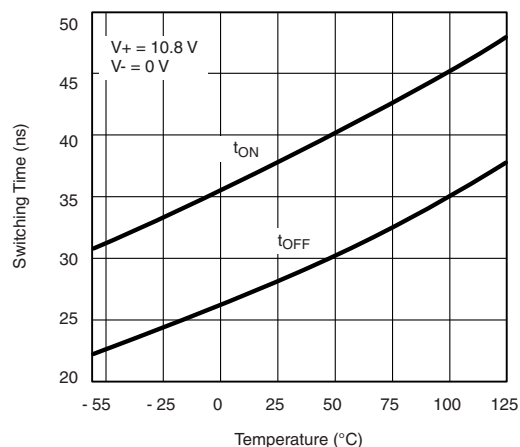
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



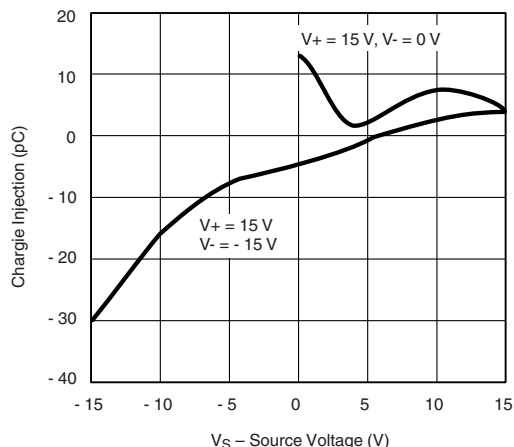
Switching Times vs. Temperature



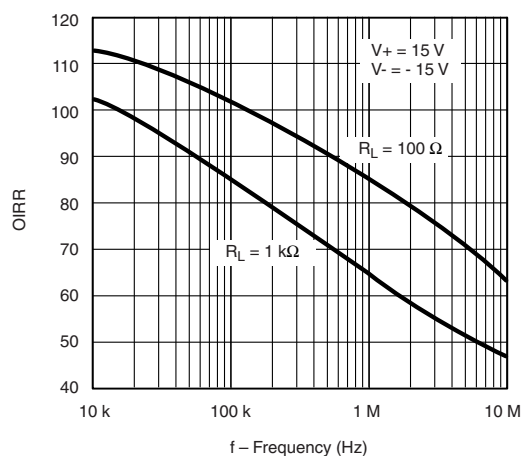
Switching Times vs. Temperature



Switching Times vs. Temperature

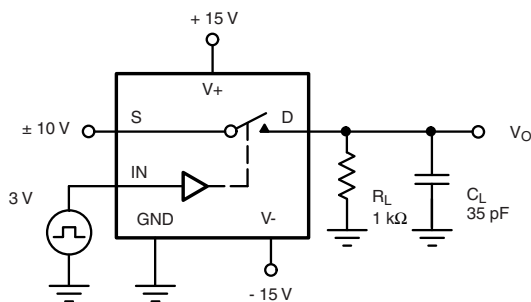


Charge Injection vs. Source Voltage

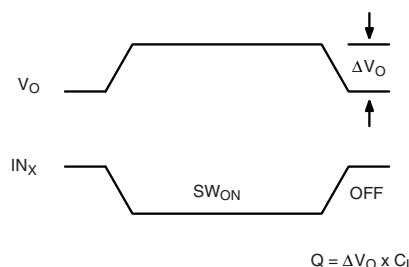
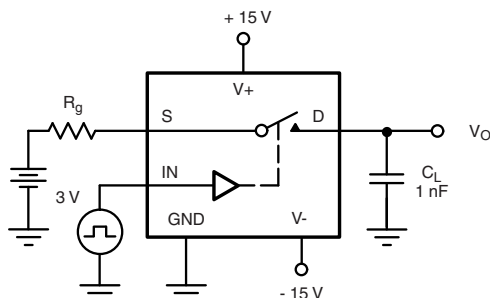
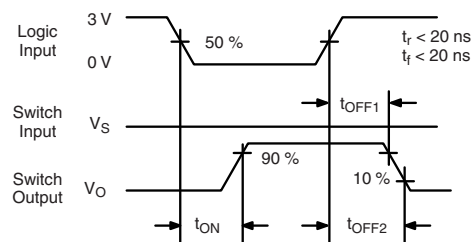
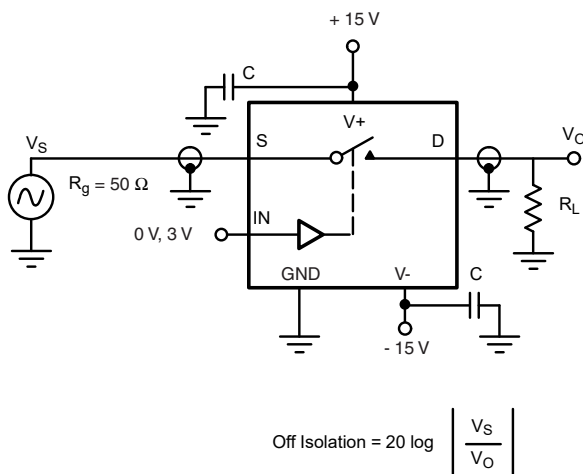


Off Isolation vs. Frequency

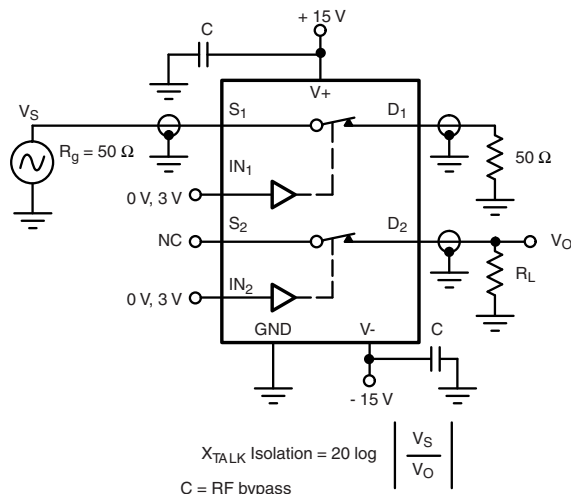
TEST CIRCUITS


 C_L (includes fixture and stray capacitance)

$$V_O = V_S \frac{R_L}{R_L + r_{DS(on)}}$$

Fig. 2 - Switching Time

Fig. 3 - Charge Injection


$$\text{Off Isolation} = 20 \log \left| \frac{V_S}{V_O} \right|$$

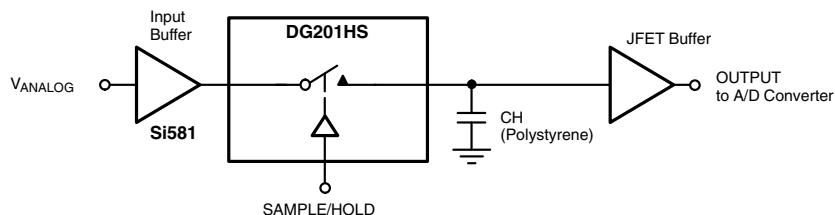
Fig. 4 - Off Isolation


$$X_{\text{TALK Isolation}} = 20 \log \left| \frac{V_S}{V_O} \right|$$

 $C = \text{RF bypass}$
Fig. 5 - Crosstalk

APPLICATIONS

A high-speed, low-glitch analog switch such as Vishay Siliconix's DG201HS improves the accuracy and shortens the acquisition and settling times of a sample-and-hold circuit.





PRODUCT SUMMARY			
Part number	DG201HS	DG201HS	DG201HS
Status code	2	2	2
Configuration	SPST x 4, NC	SPST x 4, NC	SPST x 4, NC
Single supply min. (V)	5	5	5
Single supply max. (V)	36	36	36
Dual supply min. (V)	5	5	5
Dual supply max. (V)	22	22	22
On-resistance (Ω)	25	25	25
Charge injection (pC)	-5	-5	-5
Source on capacitance (pF)	-	-	-
Source off capacitance (pF)	8	8	8
Leakage switch on typ. (nA)	0.1	0.1	0.1
Leakage switch off max. (nA)	1	1	1
-3 dB bandwidth (MHz)	-	-	-
Package	TSSOP-16	SO-16 (narrow) AS	Plastic DIP-16
Functional circuit / applications	Multi purpose, instrumentation, medical and healthcare	Multi purpose, instrumentation, medical and healthcare	Multi purpose, instrumentation, medical and healthcare
Interface	Parallel	Parallel	Parallel
Single supply operation	Yes	Yes	Yes
Dual supply operation	Yes	Yes	Yes
Turn on time max. (ns)	50	50	50
Crosstalk and off isolation	-85	-85	-85

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